Watanabe et al.					
[54]	THIN FILE	M EL DEVICE WITH PROTECTIVE			
• •	FILM				
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[57] ABSTRACT

A thin-film EL device of which the surface is coated with a protective film of a two-layer structure consisting of an insulating film (10) and a metallic film (20) in order to obtain good air-tightness and high reliability. The insulating film (10) consists of any one of a silicon oxide film, a silicon nitride film, an aluminum oxide film or a tantalum oxide film, and the metallic film consists of a thin film of either aluminum or tantalum.

6 Claims, 6 Drawing Sheets

